## **Vishay Semiconductors**

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Hyperfast Rectifier, 30 A FRED Pt<sup>®</sup> G5



## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I <sub>F(AV)</sub>	30 A							
V <sub>R</sub>	600 V							
V <sub>F</sub> at I <sub>F</sub> at 125 °C	1.15 V							
t <sub>rr</sub> (typ.)	25 ns							
T <sub>J</sub> max.	175 °C							
Package	TO-220AC 2L							
Circuit configuration	Single							

### **FEATURES**

- · Best in class forward voltage drop and switching losses trade off
- · Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- AEC-Q101 qualified, meets JESD 201 class 1A whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV on-board battery chargers

## **MECHANICAL DATA**

Case: TO-220AC 2L Molding compound meets UL 94 V-0 flammability rating

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Repetitive peak reverse voltage	V <sub>RRM</sub>		600	V					
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 113 °C, D = 0.50	30	A					
Repetitive peak forward current	I <sub>FRM</sub>	T <sub>C</sub> = 113 °C, D = 0.50, f = 20 kHz	60						
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_{C}$ = 25 °C, $t_{p}$ = 10 ms, sine wave	330						
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	۵°					

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	600	-	-				
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 30 A	-	1.3	1.6	V			
		I <sub>F</sub> = 30 A, T <sub>J</sub> = 125 °C	-	1.15	-				
	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	-	20				
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA			
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	36	-	pF			
Series inductance	L <sub>S</sub>	Measured to lead 5 mm from package body	-	8	-	nH			



COMPLIANT

HALOGEN FREE



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DYNAMIC RECOVERY CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		I <sub>F</sub> = 1.0 A,dI <sub>F</sub> /dt =	$I_F = 1.0 \text{ A,} dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$			-				
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	41	-	ns			
		T <sub>J</sub> = 125 °C		-	58	-				
Peak recovery current		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 20 A dI <sub>F</sub> /dt = 1000 A/µs	-	19	-	A			
	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm B} = 400 \text{ V}$	-	32	-				
	0	T <sub>J</sub> = 25 °C		-	419	-	nC			
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	1176	-				
		T <sub>J</sub> = 25 °C		-	46	-	ns			
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C	-	-	65	-				
Deals receivers ourrent		T <sub>J</sub> = 25 °C	$I_F = 30 A$	-	21	-	A			
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 1000 A/µs V <sub>B</sub> = 400 V	-	36	-				
D	0	T <sub>J</sub> = 25 °C		-	550	-				
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	1560	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	1.3	°C/W				
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C				
Marking device		Case style TO-220AC 2L	E5TH3006TH							



# VS-E5TH3006THN3

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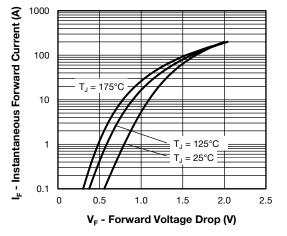


Fig. 1 - Forward Voltage Drop Characteristics, Per Leg

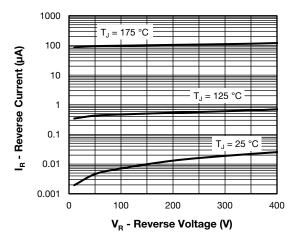


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage, Per Leg

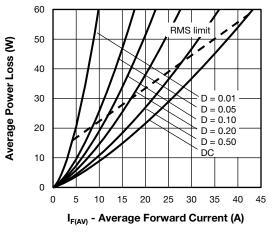


Fig. 5 - Forward Power Loss Characteristics, Per Leg

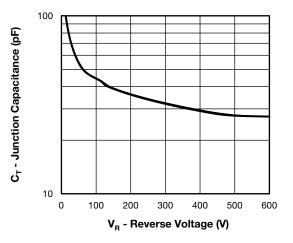


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage, Per Leg

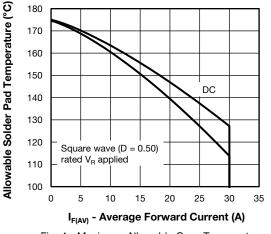


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current, Per Leg

#### **VS-E5TH3006THN3** www.vishay.com **Vishay Semiconductors** 10 Z<sub>thJC</sub> - Thermal Impedance Junction to Case (°C/W) 1 0.50 0.1 0.20 0.10 0.05 0.02 DC 0.01 0.01 0.00001 0.0001 0.001 0.01 0.1 1 t<sub>1</sub> - Rectangular Pulse Duration (s)

Fig. 6 - Transient Thermal Impedance, Junction to Case, Per Leg

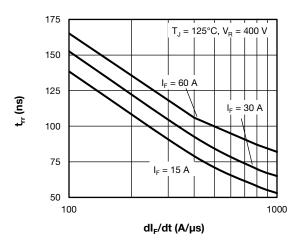


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt, Per Leg

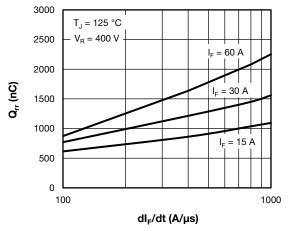


Fig. 8 - Typical Reverse Recovery Charge vs. dl<sub>F</sub>/dt, Per Leg

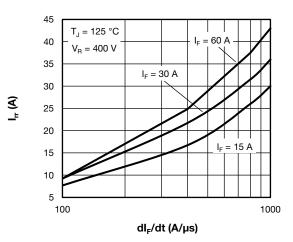


Fig. 9 - Typical Reverse Recovery Current vs. dl<sub>F</sub>/dt, Per Leg

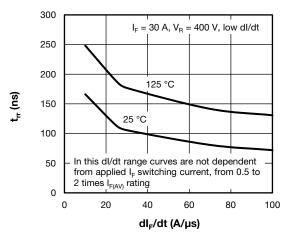


Fig. 10 - Typical Reverse Recovery Time vs.  $dI_F/dt$ , Per Leg

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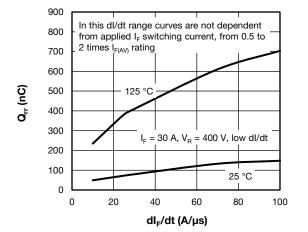
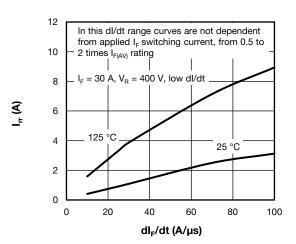


Fig. 11 - Typical Reverse Recovery Charge vs. dl<sub>F</sub>/dt, Per Leg



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Fig. 12 - Typical Reverse Recovery Current vs. dl<sub>F</sub>/dt, Per Leg

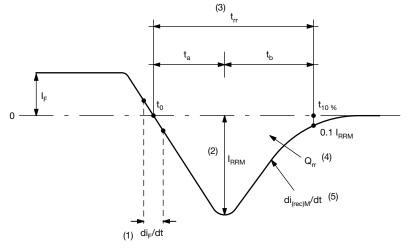


Fig. 13 - Reverse Recovery Waveform and Definitions

#### Notes

- <sup>(1)</sup> di<sub>F</sub>/dt rate of change of current through zero crossing
- <sup>(2)</sup> I<sub>RRM</sub> peak reverse recovery current
- $^{(3)}$  t<sub>rr</sub> reverse recovery time measured from t<sub>0</sub>, crossing point of negative going I<sub>F</sub>, to point t<sub>10%</sub>, 0.1 I<sub>RRM</sub>
- $^{(4)}~~Q_{rr}$  area under curve defined by  $t_0$  and  $t_{10~\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

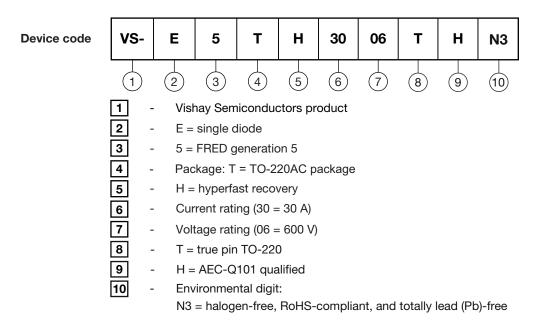
 $^{(5)}$  di<sub>(rec)</sub>M/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>



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### **ORDERING INFORMATION TABLE**



ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-E5TH3006THN3	50	1000	Antistatic plastic tube						

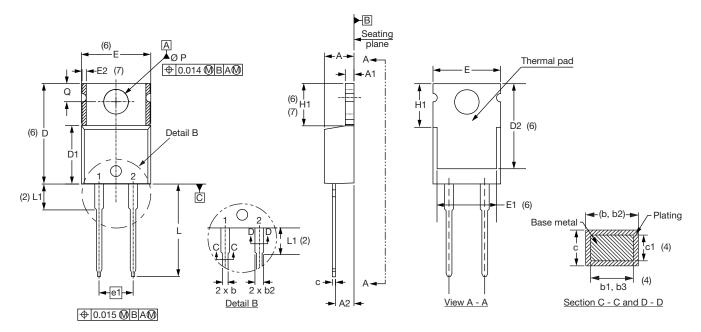
LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96069						
Part marking information	www.vishay.com/doc?95391						
SPICE model	www.vishay.com/doc?96919						



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2L TO-220AC

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	SVM	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			e1	4.88	5.28	0.192	0.208	
b	0.69	1.01	0.027	0.040			H1	5.84	6.86	0.230	0.270	6, 7
b1	0.38	0.97	0.015	0.038	4		L	13.52	14.02	0.532	0.552	
b2	1.20	1.73	0.047	0.068			L1	3.32	3.82	0.131	0.150	2
b3	1.14	1.73	0.045	0.068	4		ØР	3.54	3.73	0.139	0.147	
с	0.36	0.61	0.014	0.024			Q	2.60	3.00	0.102	0.118	
c1	0.36	0.56	0.014	0.022	4							
D	14.85	15.25	0.585	0.600	3							
D1	8.38	9.02	0.330	0.355								
D2	11.68	12.88	0.460	0.507	6							
E	10.11	10.51	0.398	0.414	3, 6							

Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

<sup>(4)</sup> Dimension b1, b3 and c1 apply to base metal only

<sup>(5)</sup> Controlling dimension: inches

<sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2 and E1

- $^{\left(7\right)}$  Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- <sup>(8)</sup> Outline conforms to JEDEC<sup>®</sup> TO-220, except D2, where JEDEC<sup>®</sup> minimum is 0.480"

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